

Product Overview

NGTB40N120L3: IGBT, Ultra Field stop - 1200V 40A, Low VCEsat

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Ultra Field Stop Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for motor driver applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Ultra Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for Low VCEsat
- These are Pb-Free Devices

Applications

- Motor Drive Inverter
- Industrial Switching
- Welding

End Products

- Industrial

For more information please contact your local sales support at www.onsemi.com.

Created on: 10/23/2021